

## **DHPT 1.2 Status**

VXD Workshop, Santander  
September 14-16, 2016

- DHPT 1.2 chips delivered end of July (100 pcs.)
- Started with test on probe station (needle card)
- DHE software needed to be changed because of wrong JTAG ID (bug in DHPT JTAG register implementation)
- Used DHH emulator for first tests (not having full coverage)

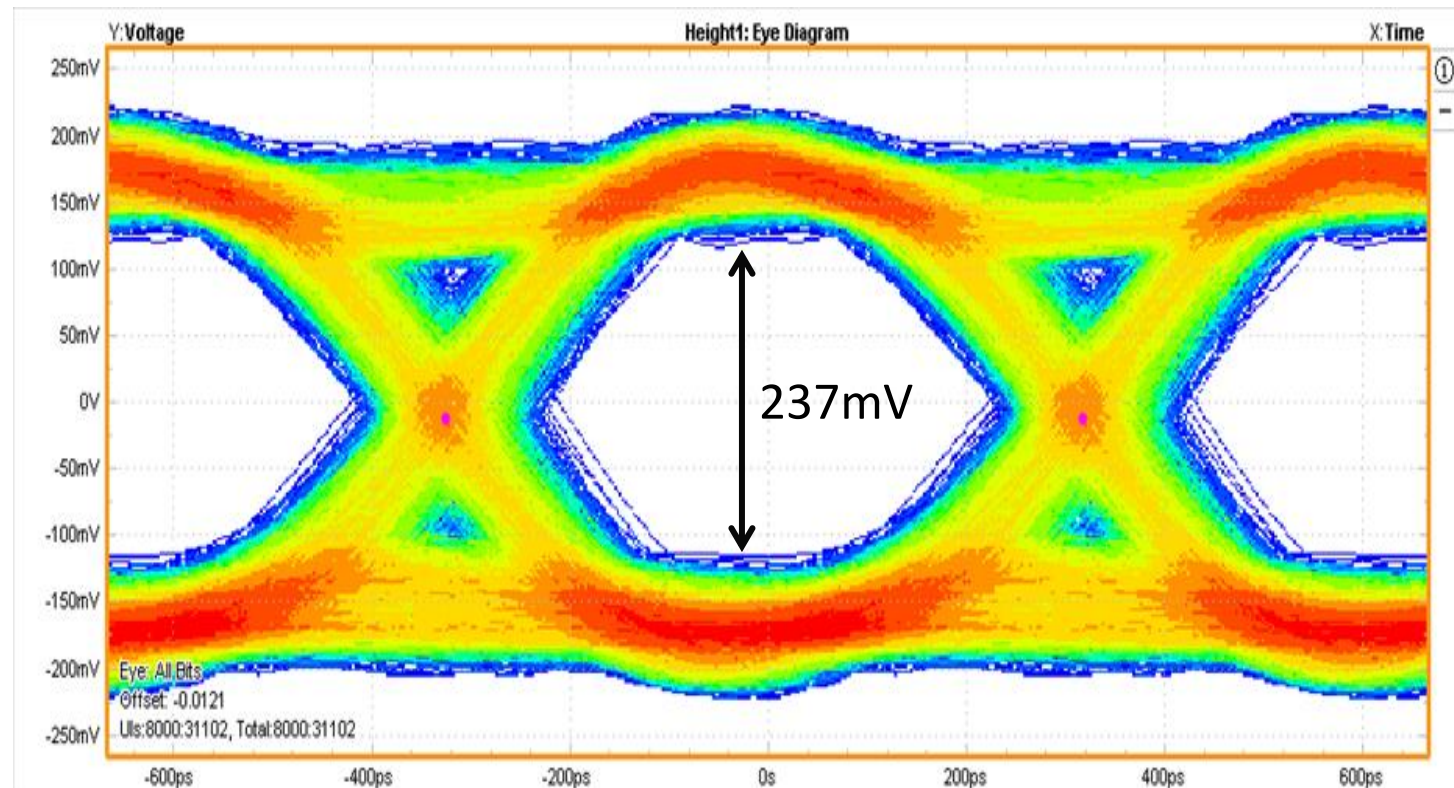
## CML Driver

- CML driver power routing
  - Ground rail (VSS) had a too high wiring resistance ( $\sim 30 \text{ Ohm}$ ), parasitic extraction did not spot this because of substrate model
  - Rerouting of power nets  $\rightarrow R_{VSS} < 0.2 \text{ Ohm}$
- CML driver bias routing
  - Removed ESD resistor in bias connection and reduced parasitic resistance  $\rightarrow$  increase of bias current, less sensitivity to voltage supply

### Test Results

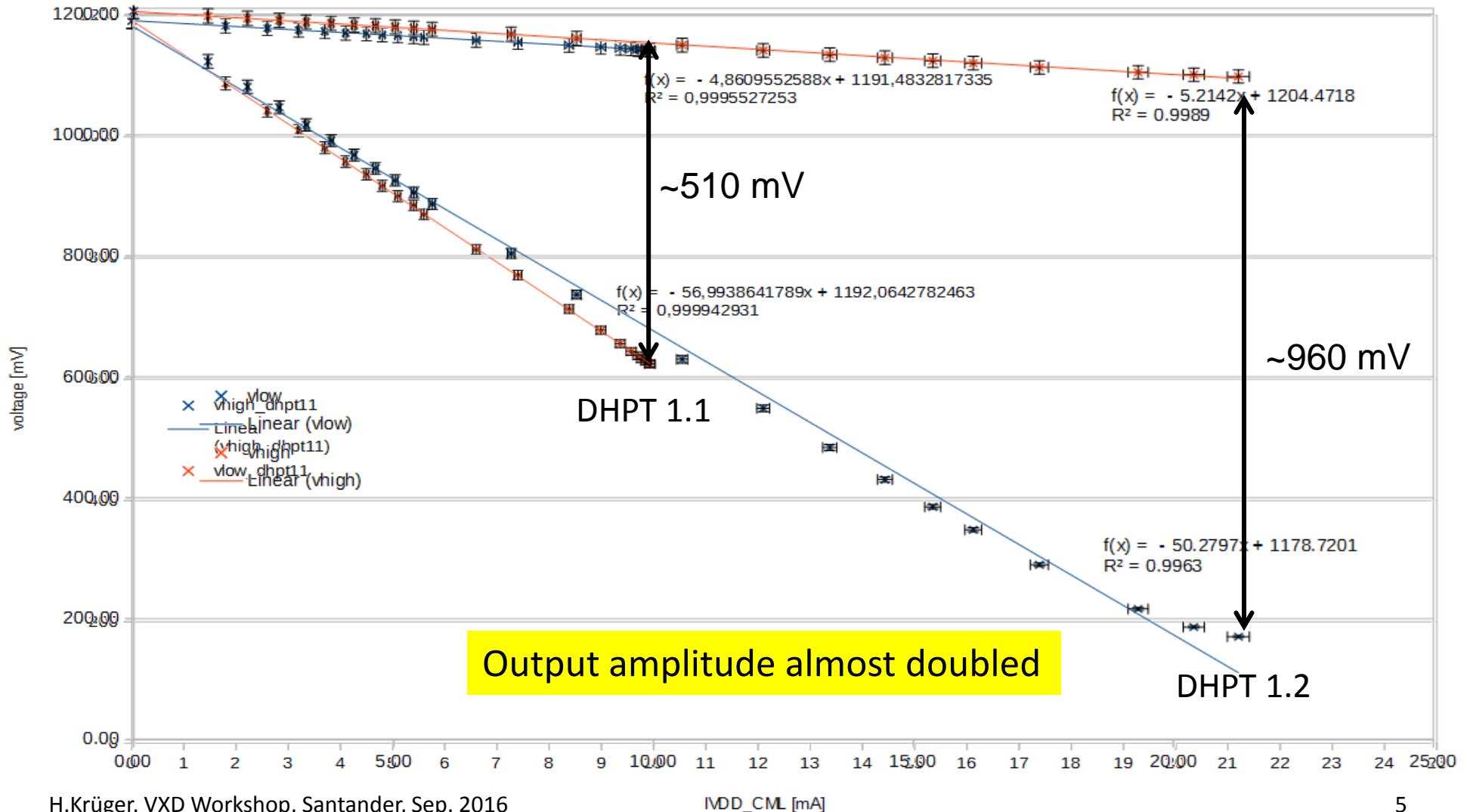


- Eyediagram with 10m Infiniband cable
  - IBIAS = 20, IBIASD = 60, Pll\_cml\_dly =2 (still a lot of headroom)



# CML Performance Comparison

- CML output high and low level as a function of IBIAS (w/o termination)



## Digital core

- Mem dump
  - Data had some low probability to show corrupted values for the first few pixels when output was set to 800 MHz and clock compensation was on  
→ fixed in HDL code
- Internal system clock phase
  - The core clock started with an arbitrary phase after power-on  
→ added controlled reset (delayed GCK) to the internal clock divider
- Gated mode sequence put out first word twice
  - Fixed HDL code

### Test Results

pending



## Digital core

- JTAG USERID changed: allows recognition of DHPT version
  - Implementation failure: used forbidden ID = xxx2 → (bit 0 of the IDCODE has to be 1)
- Gated mode: DATA\_IN for the switcher can be selected to be controlled from either the *normal mode* sequence of the *gated mode* sequence (was *normal mode* only)
- Added the DHPT ID in the memory dump frame header
- Memory dump start address configurable
- Bias register for LVDS receivers has fixed minimum value

## Test Results

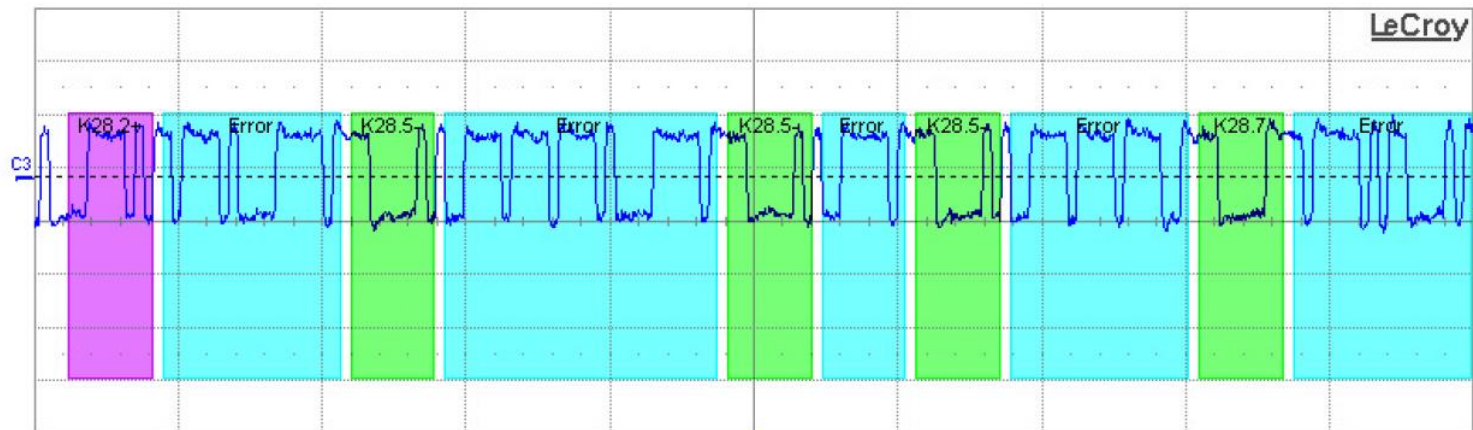


pending

pending



- We have seen an issue with the data link between DHE and DHPT 1.2
- DHPT 1.2 puts out invalid symbols → link does not synchronize



DHPT 1.2 data link @ DHE

- Very recent finding, need to cross-check with DHH emulator
- Behavior not reproducible in simulation (full layout, all corners)

- DHPT 1.2 changes
  - Power routing if the CML driver fixed successfully
  - Re-synthesized the digital core (bug fixes and enhancements)
  - Update of JTAG User ID introduced a bug in this register (User ID = 0 like DHP 0.2)
- Functional test (ongoing)
  - Functional test on probe station, test PCB, and hybrid 5
  - Issue with the data link synchronization needs to be understood
- Mass production/testing
  - Decision for DHPT 1.2 as the production chip
  - Then: Order of 9 additional wafers (1000 chips in total)
  - Two new needle cards for probe station testing are available
  - Estimated testing throughput: ~50 chips per week

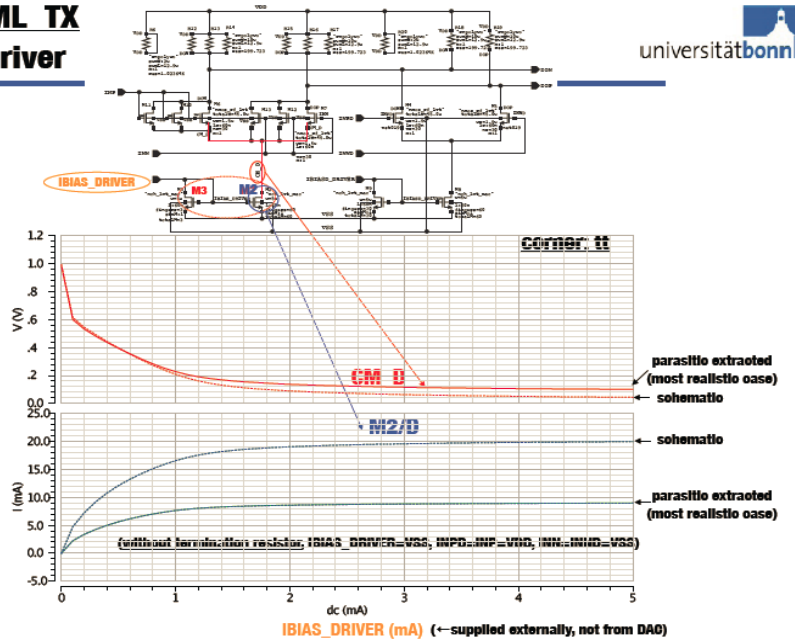
# BACKUP

# DHPT CML Driver

- Changes from DHPT1.0 to DHPT1.1

## DHPT10 CML TX Main driver

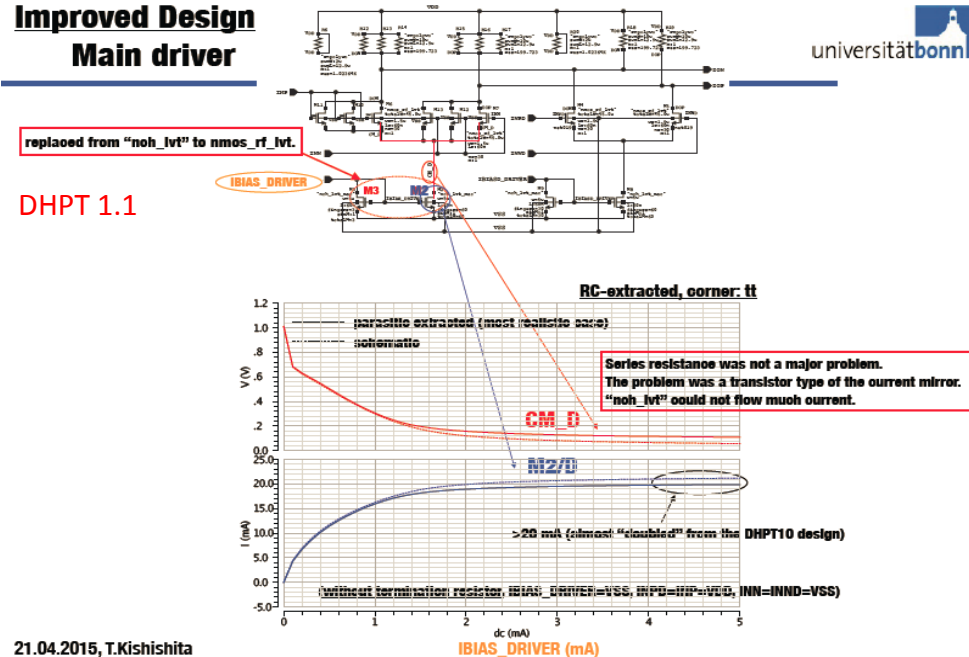
DHPT 1.0



06.05.2015, T.Kishishita

## Improved Design Main driver

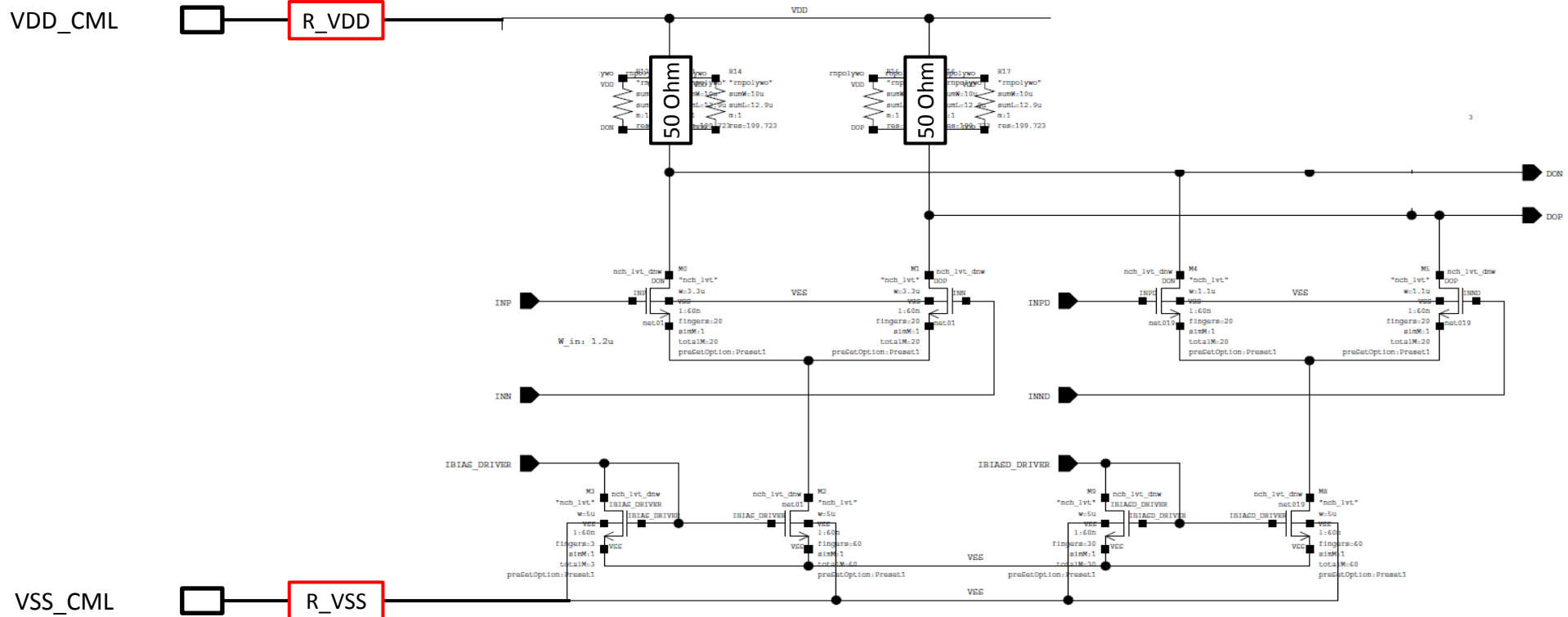
DHPT 1.1



21.04.2015, T.Kishishita

- Layout extracted with all parasitic elements
- Current in the main stage expected to be ~20mA after improvement of the transistor layout
- However measurements on DHPT 1.1 indicated ~10mA only

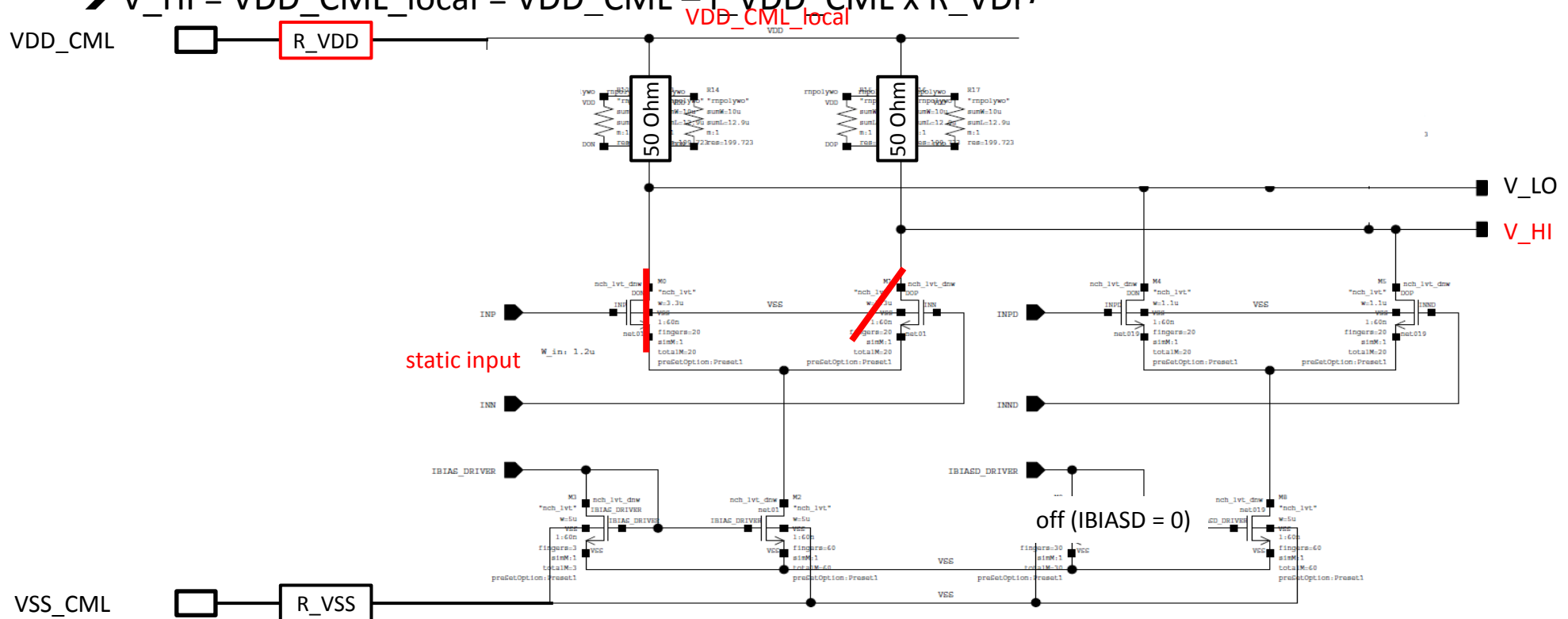
- Possible explanation: layout extraction underestimated the **parasitic** resistances  $R_{VDD}$  and  $R_{VSS}$  on the power lines



# Measurement of the Parasitic Resistance R\_VDD

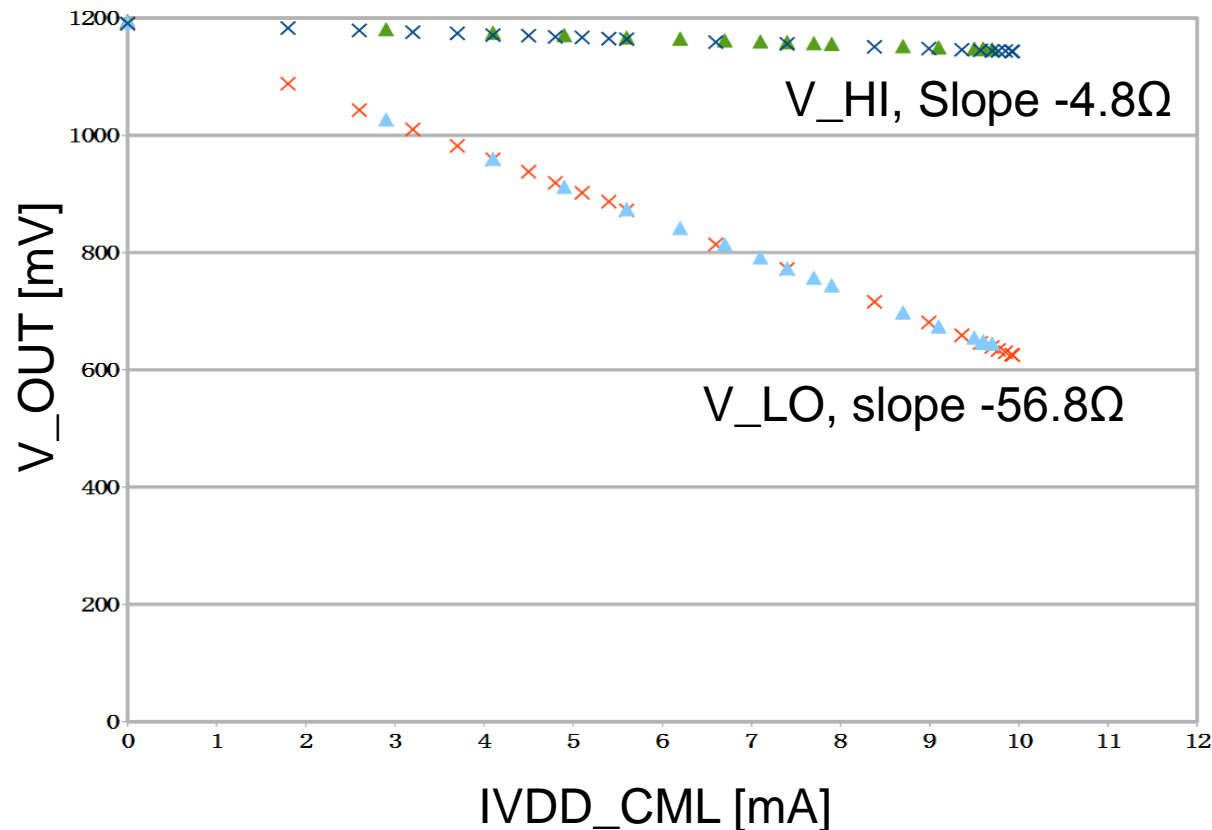
- Measure  $V_{HI}$  as a function of  $I_{VDD\_CML}$  by changing  $IBIAS$ 
  - no termination at driver output
  - no data line switching

→  $V_{HI} = VDD\_CML\_local = VDD\_CML - I_{VDD\_CML} \times R_{VDD}$



# Measurement of the Parasitic Resistance R\_VDD

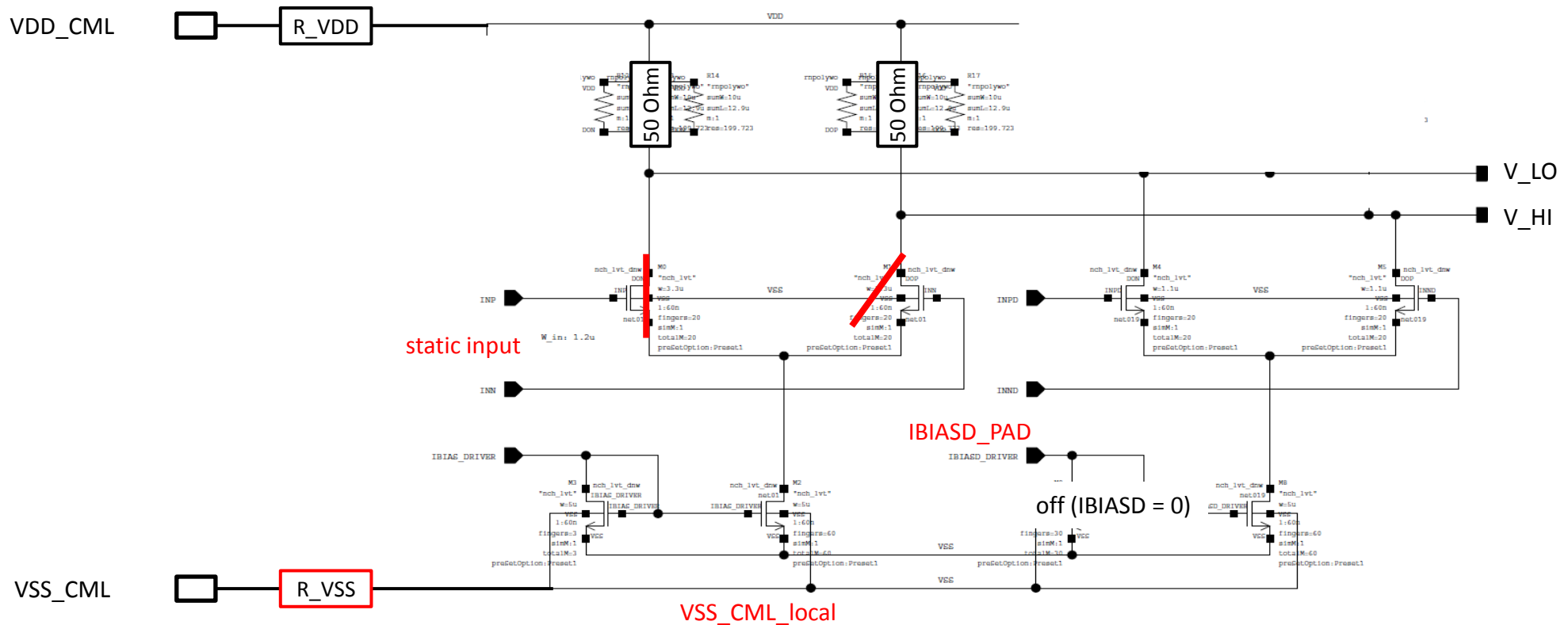
- Measurements indicate a parasitic resistance of about 5 Ohm in the VDD\_CML line
- This is in agreement with the extraction of the parasitic elements of the layout, however this does not explain the loss of drive strength.



DHPT 1.0: ▲ ▲  
DHPT 1.1: x x

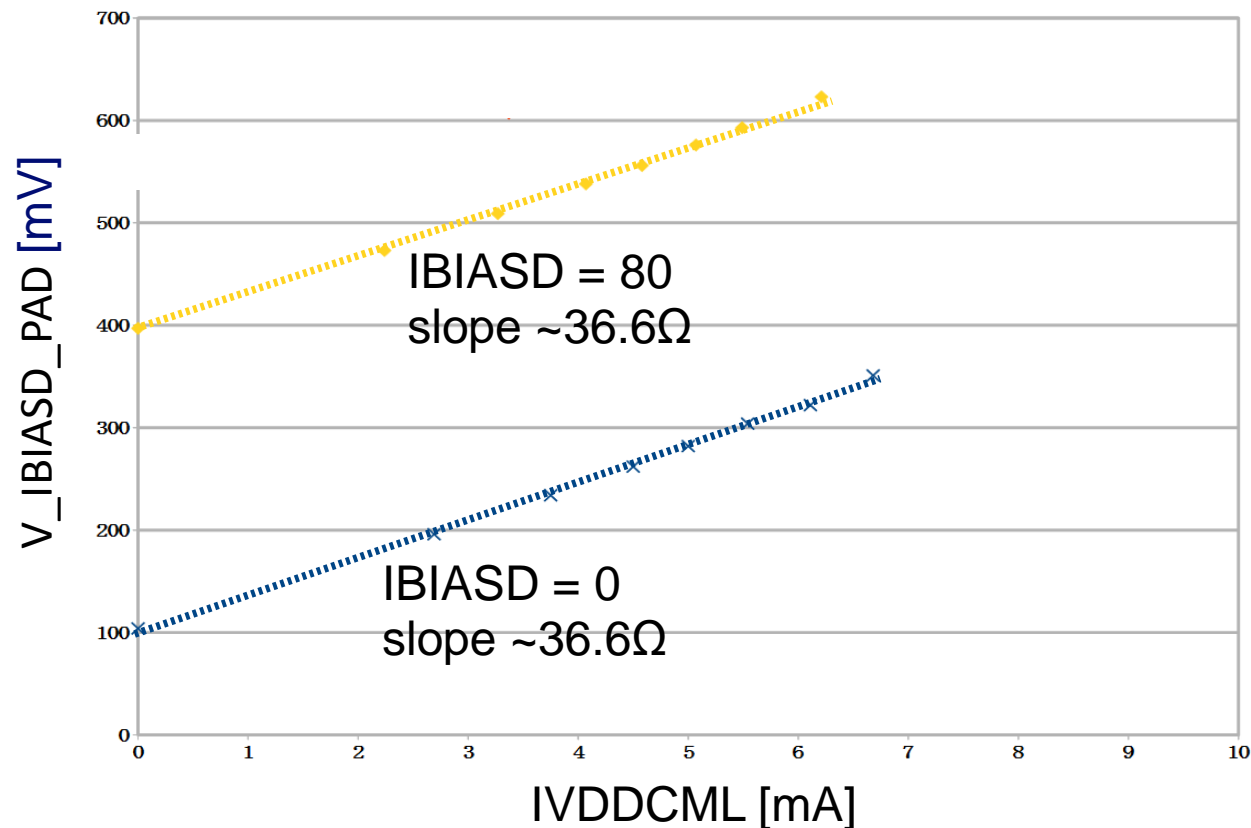
# Measurement of the Parasitic Resistance R\_VSS

- Measure V\_IBIASD\_PAD as a function of I\_VDD\_CML by changing IBIAS, no termination at driver output
- $V\_IBIASD\_PAD = VSS\_CML\_local + const = VSS\_CML + I\_VDD\_CML \times R\_VSS$



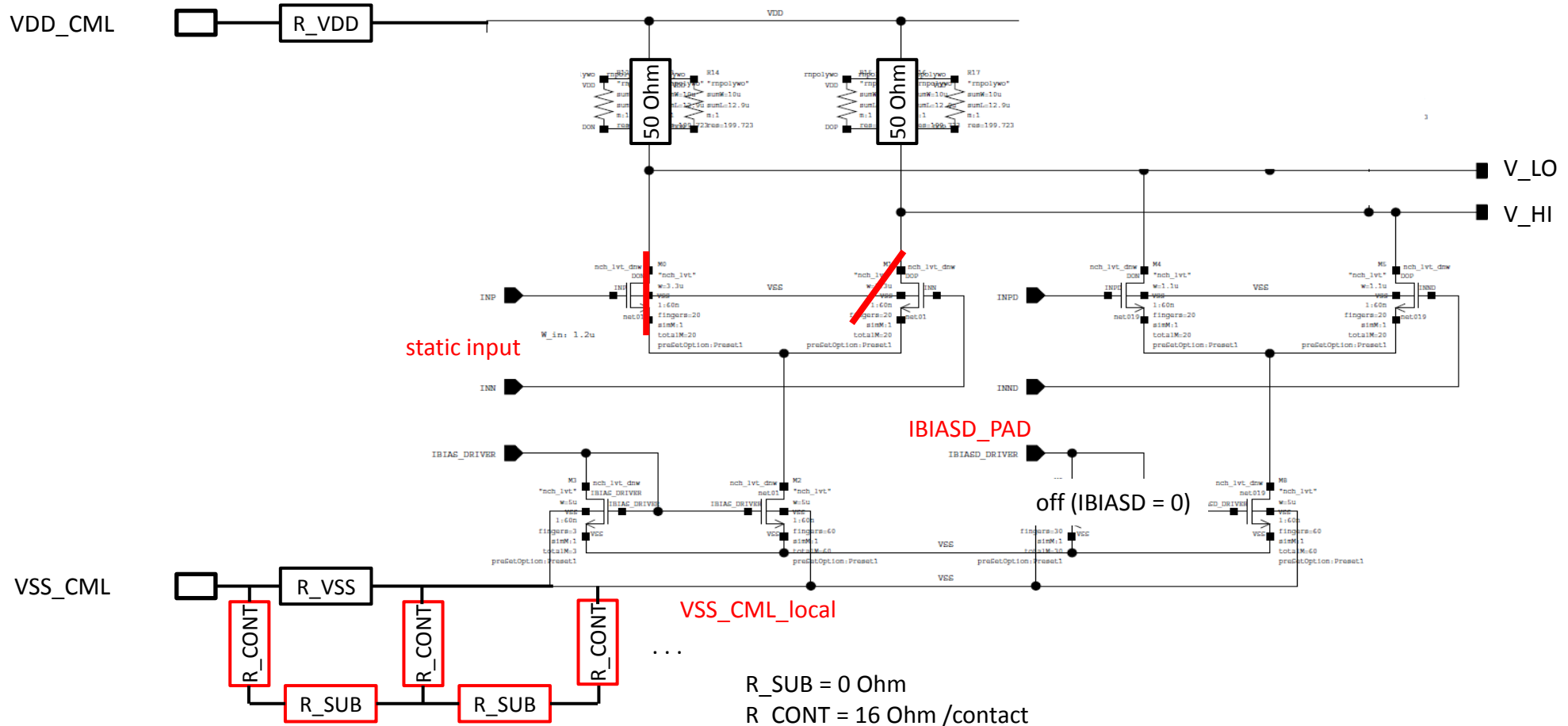
# Measurement of the Parasitic Resistance R\_VSS

- Measurements indicate a parasitic resistance of about 36 Ohm in the VSS\_CML line
- This is **not in agreement** with the simulation of the extracted layout which also shows ~5 Ohm parasitic resistance



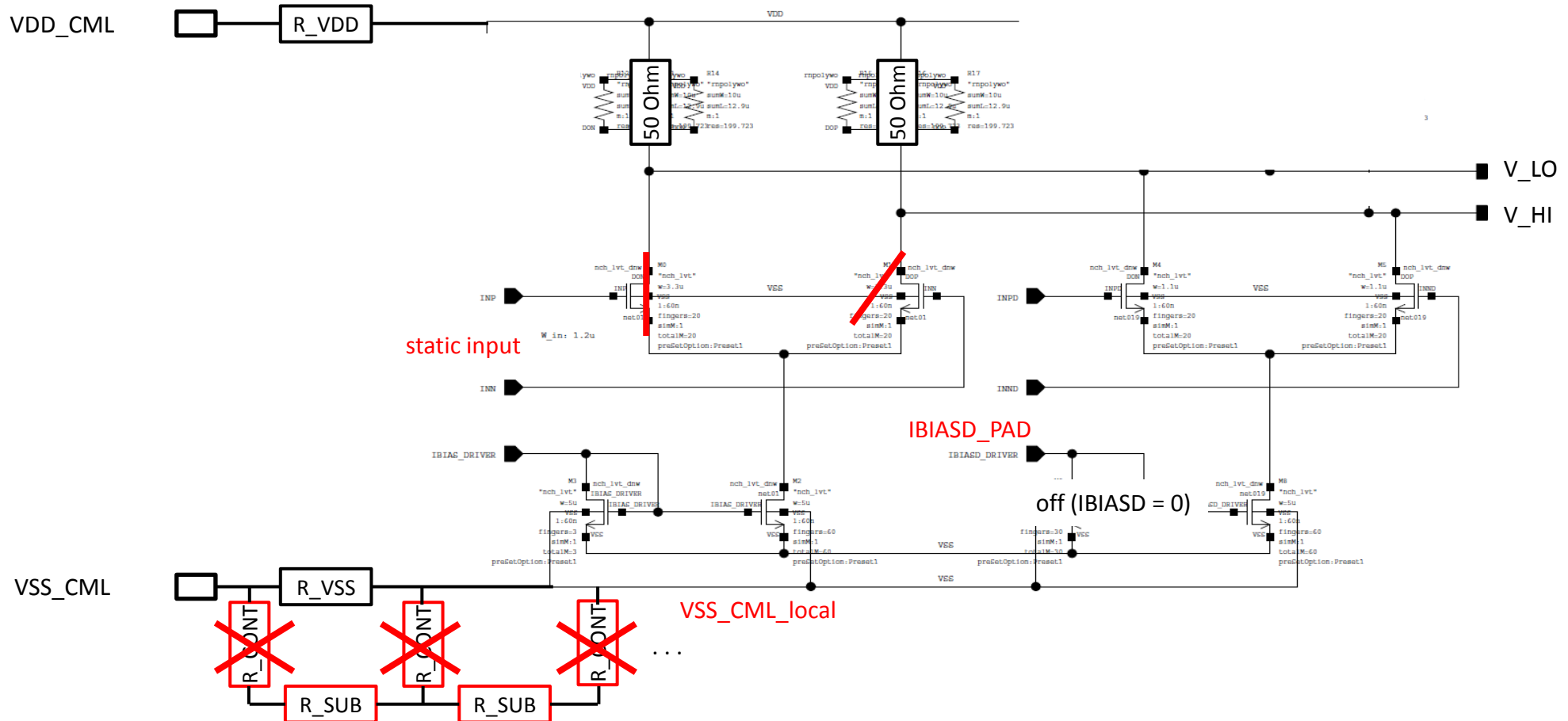
# Issue with the RC-extraction of the layout

- The extraction tool models the silicon substrate as a perfect conductor ( $R_{SUB} = 0 \text{ Ohm}$ ) and VSS\_CML ins connected to the bulk with a lot of substrate contacts
- ➔ Underestimation of the resistance in VSS\_CML



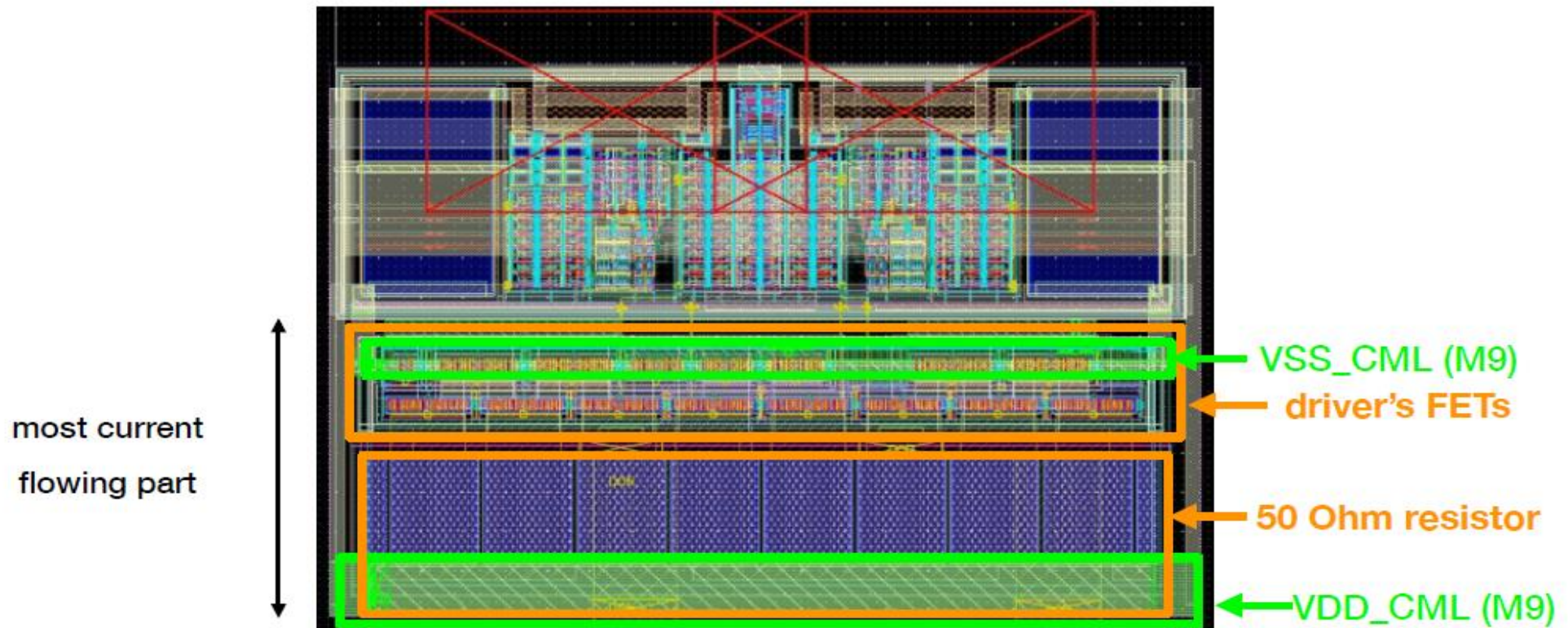
# Proof of the Explanation

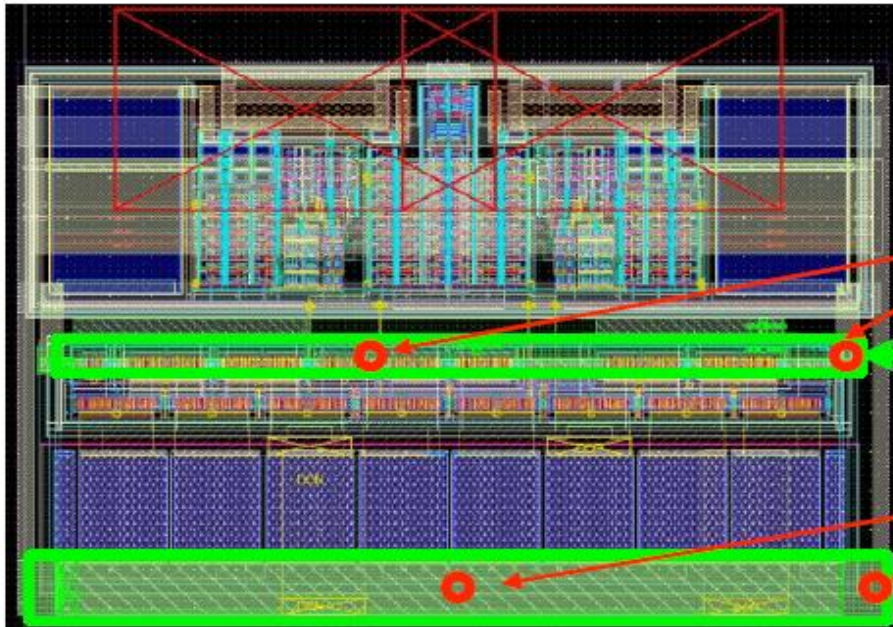
- We removed the substrate contacts in the layout and extracted the parasitics again  
 $\rightarrow R_{VSS\_CML} \sim 30 \text{ Ohm}$



# CML\_TX Layout toward DHPT12

- vertical connection (M2→M9 for VDD\_CML and M4→M9 for VSS\_CML)
- separate VSS and PSUB for Driver current mirror and switches
- avoid M1 connection between separate circuit blocks





check the resistance between these points (M9→M4)

VSS\_CML

check the resistance between these points (M9→M2)

VDD\_CML

	Assura, typical	Assura, worst	Calibre, typical
VDD_CML	49.3 m $\Omega$	66.5 m $\Omega$	53.0 m $\Omega$
VSS_CML	114.1 m $\Omega$	151.4 m $\Omega$	115.2 m $\Omega$

$\Delta R_{\text{serial}}$ : ~30% corner dependence, and ~10% between Assura and Calibre